Preferred Device

# Programmable Unijunction Transistor

# **Programmable Unijunction Transistor Triggers**

Designed to enable the engineer to "program" unijunction characteristics such as RBB,  $\eta$ , IV, and Ip by merely selecting two resistor values. Application includes thyristor–trigger, oscillator, pulse and timing circuits. These devices may also be used in special thyristor applications due to the availability of an anode gate. Supplied in an inexpensive TO–92 plastic package for high–volume requirements, this package is readily adaptable for use in automatic insertion equipment.

- Programmable R<sub>BB</sub>, η, I<sub>V</sub> and I<sub>P</sub>
- Low On–State Voltage 1.5 Volts Maximum @ I<sub>F</sub> = 50 mA
- Low Gate to Anode Leakage Current 10 nA Maximum
- High Peak Output Voltage 11 Volts Typical
- Low Offset Voltage 0.35 Volt Typical (R<sub>G</sub> = 10 k ohms)
- Device Marking: Logo, Device Type, e.g., 2N6027, Date Code

#### **MAXIMUM RATINGS** (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit		
*Power Dissipation Derate Above 25°C	PF 1/θ <sub>JA</sub>	300 4.0	mW mW/°C		
*DC Forward Anode Current Derate Above 25°C	lΤ	150 2.67	mA mA/°C		
*DC Gate Current	IG	±50	mA		
Repetitive Peak Forward Current 100 μs Pulse Width, 1% Duty Cycle *20 μs Pulse Width, 1% Duty Cycle	ITRM	1.0 2.0	Amps		
Non-Repetitive Peak Forward Current 10 μs Pulse Width	ITSM	5.0	Amps		
*Gate to Cathode Forward Voltage	VGKF	40	Volts		
*Gate to Cathode Reverse Voltage	VGKR	-5.0	Volts		
*Gate to Anode Reverse Voltage	VGAR	40	Volts		
*Anode to Cathode Voltage(1)	VAK	±40	Volts		
Operating Junction Temperature Range	ТЈ	-50 to +100	°C		
*Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C		

<sup>\*</sup>Indicates JEDEC Registered Data



#### **ON Semiconductor**

http://onsemi.com

PUTs 40 VOLTS 300 mW





TO-92 (TO-226AA) CASE 029 STYLE 16

PIN ASSIGNMENT				
1 Anode				
2	Gate			
3	Cathode			

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.



<sup>(1)</sup> Anode positive, R<sub>GA</sub> = 1000 ohms Anode negative, R<sub>GA</sub> = open

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	75	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Maximum Lead Temperature for Soldering Purposes (<1/16" from case, 10 secs max)	TL	260	°C

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Fig. No.	Symbol	Min	Тур	Max	Unit	
*Peak Current (Vs = 10 Vdc, RG = 1 M $\Omega$ ) (Vs = 10 Vdc, RG = 10 k ohms)	2N6027 2N6028 2N6027 2N6028	2,9,11	lp		1.25 0.08 4.0 0.70	2.0 0.15 5.0 1.0	μА
*Offset Voltage $(V_S = 10 \text{ Vdc}, R_G = 1 \text{ M}\Omega)$ $(V_S = 10 \text{ Vdc}, R_G = 10 \text{ k ohms})$	2N6027 2N6028 (Both Types)	1	VT	0.2 0.2 0.2	0.70 0.50 0.35	1.6 0.6 0.6	Volts
*Valley Current $(V_S = 10 \text{ Vdc}, R_G = 1 \text{ M}\Omega)$ $(V_S = 10 \text{ Vdc}, R_G = 10 \text{ k ohms})$ $(V_S = 10 \text{ Vdc}, R_G = 200 \text{ ohms})$	2N6027 2N6028 2N6027 2N6028 2N6027 2N6028	1,4,5	IV	— 70 25 1.5	18 18 150 150 — —	50 25 — — —	μA mA
*Gate to Anode Leakage Current (V <sub>S</sub> = 40 Vdc, T <sub>A</sub> = 25°C, Cathode Open) (V <sub>S</sub> = 40 Vdc, T <sub>A</sub> = 75°C, Cathode Open)		_	<sup>I</sup> GAO		1.0 3.0	10 —	nAdc
Gate to Cathode Leakage Current (VS = 40 Vdc, Anode to Cathode Shorted)		_	<sup>I</sup> GKS	_	5.0	50	nAdc
*Forward Voltage (I <sub>F</sub> = 50 mA Peak) <sup>(1)</sup>		1,6	٧F	_	0.8	1.5	Volts
*Peak Output Voltage $(V_G = 20 \text{ Vdc}, C_C = 0.2 \mu\text{F})$		3,7	Vo	6.0	11	_	Volt
Pulse Voltage Rise Time $(V_B = 20 \text{ Vdc}, C_C = 0.2 \mu\text{F})$		3	t <sub>r</sub>	_	40	80	ns

<sup>\*</sup>Indicates JEDEC Registered Data

http://onsomi.com

<sup>(1)</sup> Pulse Test: Pulse Width  $\leq 300~\mu sec,~Duty~Cycle \leq 2\%.$ 

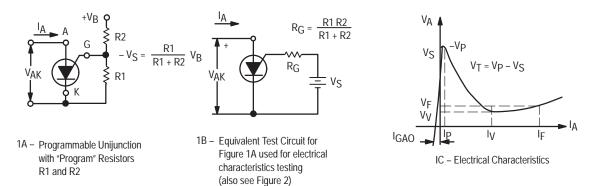


Figure 1. Electrical Characterization

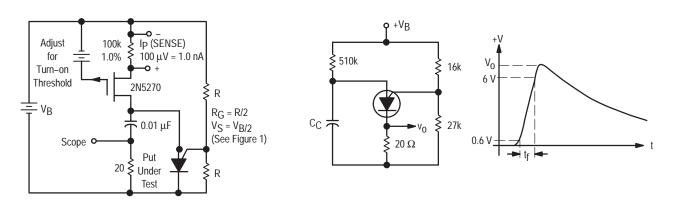


Figure 2. Peak Current (Ip) Test Circuit

Figure 3. Vo and tr Test Circuit

#### **TYPICAL VALLEY CURRENT BEHAVIOR**

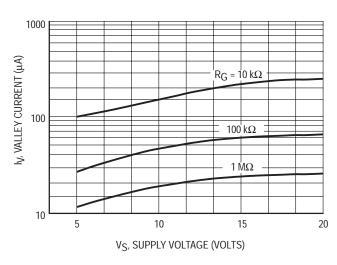
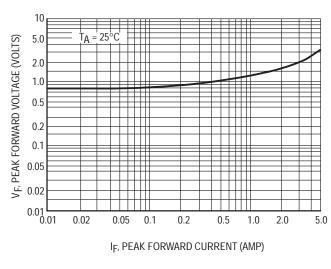


Figure 4. Effect of Supply Voltage

Figure 5. Effect of Temperature



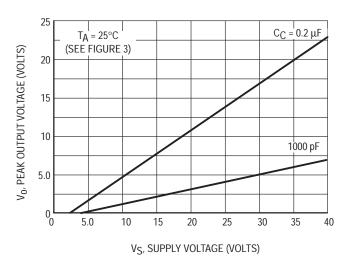


Figure 6. Forward Voltage

Figure 7. Peak Output Voltage

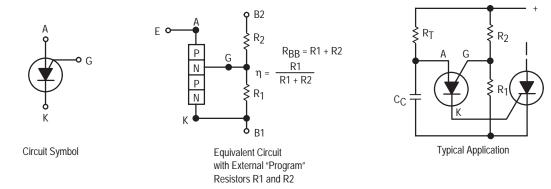
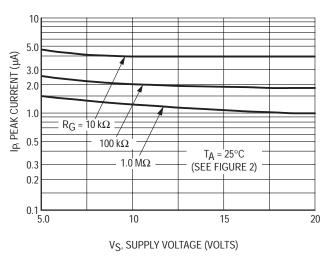


Figure 8. Programmable Unijunction

#### **TYPICAL PEAK CURRENT BEHAVIOR**

#### 2N6027



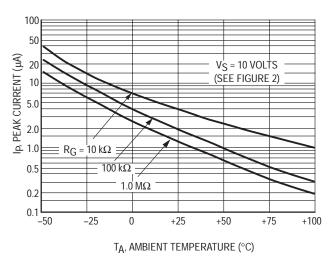
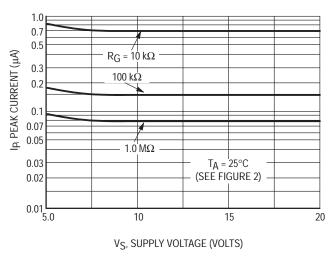


Figure 9. Effect of Supply Voltage and R<sub>G</sub>

Figure 10. Effect of Temperature and R<sub>G</sub>

#### 2N6028





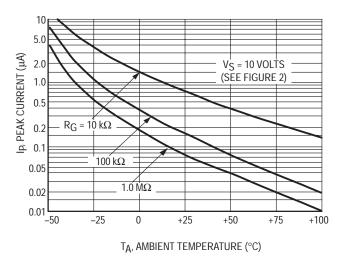


Figure 12. Effect of Temperature and RG

#### TO-92 EIA RADIAL TAPE IN FAN FOLD BOX OR ON REEL

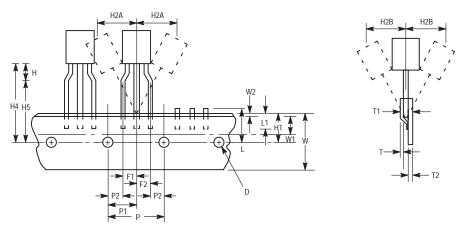


Figure 13. Device Positioning on Tape

			Specification			
		Inches		Millimeter		
Symbol	Item		Max	Min	Max	
D	Tape Feedhole Diameter	0.1496	0.1653	3.8	4.2	
D2	Component Lead Thickness Dimension	0.015	0.020	0.38	0.51	
F1, F2	Component Lead Pitch	0.0945	0.110	2.4	2.8	
Н	Bottom of Component to Seating Plane	.059	.156	1.5	4.0	
H1	Feedhole Location	0.3346	0.3741	8.5	9.5	
H2A	Deflection Left or Right	0	0.039	0	1.0	
H2B	Deflection Front or Rear	0	0.051	0	1.0	
H4	Feedhole to Bottom of Component	0.7086	0.768	18	19.5	
H5	Feedhole to Seating Plane	0.610	0.649	15.5	16.5	
L	Defective Unit Clipped Dimension	0.3346	0.433	8.5	11	
L1	Lead Wire Enclosure	0.09842	_	2.5	_	
Р	Feedhole Pitch	0.4921	0.5079	12.5	12.9	
P1	Feedhole Center to Center Lead	0.2342	0.2658	5.95	6.75	
P2	First Lead Spacing Dimension	0.1397	0.1556	3.55	3.95	
Т	Adhesive Tape Thickness	0.06	0.08	0.15	0.20	
T1	Overall Taped Package Thickness	<u> </u>	0.0567	_	1.44	
T2	Carrier Strip Thickness	0.014	0.027	0.35	0.65	
W	Carrier Strip Width	0.6889	0.7481	17.5	19	
W1	Adhesive Tape Width	0.2165	0.2841	5.5	6.3	
W2	Adhesive Tape Position	.0059	0.01968	.15	0.5	

#### NOTES:

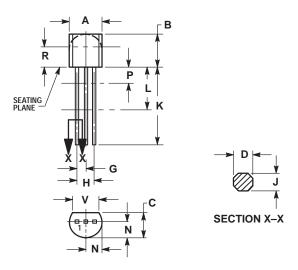
- 1. Maximum alignment deviation between leads not to be greater than 0.2 mm.
- 2. Defective components shall be clipped from the carrier tape such that the remaining protrusion (L) does not exceed a maximum of 11 mm.
- 3. Component lead to tape adhesion must meet the pull test requirements.
- 4. Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
- 5. Holddown tape not to extend beyond the edge(s) of carrier tape and there shall be no exposure of adhesive.
- 6. No more than 1 consecutive missing component is permitted.
- 7. A tape trailer and leader, having at least three feed holes is required before the first and after the last component.
- 8. Splices will not interfere with the sprocket feed holes.

#### ORDERING & SHIPPING INFORMATION: 2N6027 and 2N6028 packaging options, Device Suffix

U.S.	Europe Equivalent	Shipping	Description of TO92 Tape Orientation
2N6027, 2N6028 2N6027, 2N6028RLRA	2N6027RL1	Bulk in Box (5K/Box) Radial Tape and Reel (2K/Reel) Radial Tape and Reel (2K/Reel)	N/A, Bulk Round side of TO92 and adhesive tape visible Flat side of TO92 and adhesive tape visible
2N6028RLRM 2N6028RLRP		Radial Tape and Fan Fold Box (2K/Box) Radial Tape and Fan Fold Box (2K/Box)	Flat side of TO92 and adhesive tape visible Round side of TO92 and adhesive tape visible

#### **PACKAGE DIMENSIONS**

TO-92 (TO-226AA) CASE 029-11 **ISSUE AJ** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.021	0.407	0.533	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
٧	0.135		3.43		

STYLE 16:
PIN 1. ANODE
2. GATE
3. CATHODE

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001-800-4422-3781 Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–8549

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